



## General Description

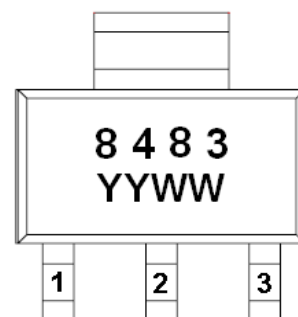
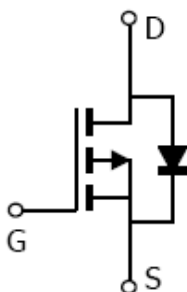
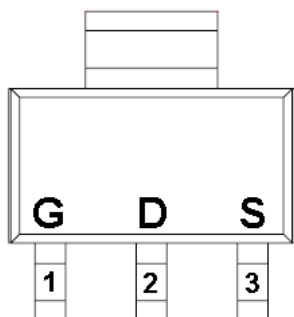
AFP8483, P-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge.

These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

## Features

- -100V/-3.8A,  $R_{DS(ON)} = 260m\Omega @ V_{GS} = -10V$
- -100V/-2.6A,  $R_{DS(ON)} = 290m\Omega @ V_{GS} = -4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- SOT-223 package design

## Pin Description ( SOT-223 )



## Application

- Motor and Load Control
- LCD TV Inverter & AD/DC Inverter Systems.
- Backlight Inverter for LCD Display
- Load Switch
- CCFL Inverter

## Pin Define

Pin	Symbol	Description
1	G	Gate
2	D	Drain
3	S	Source

## Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFP8483S223RG	8483	SOT-223	Tape & Reel	2500 EA

※ YY year code

※ WW week code

※ AFP8483S223RG : 13" Tape & Reel ; Pb- Free ; Halogen- Free



**Absolute Maximum Ratings**

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-100	V
Gate –Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	-3.8
		T <sub>A</sub> =70°C	-2.6
Pulsed Drain Current	I <sub>DM</sub>	-15	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	-5	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	2.8
		T <sub>A</sub> =70°C	1.2
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	120	°C/W

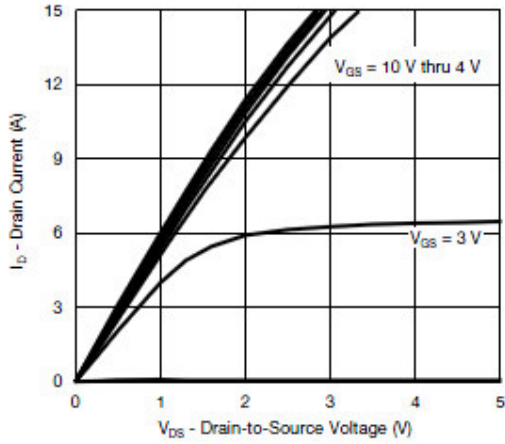
**Electrical Characteristics**

(T<sub>A</sub>=25°C Unless otherwise noted)

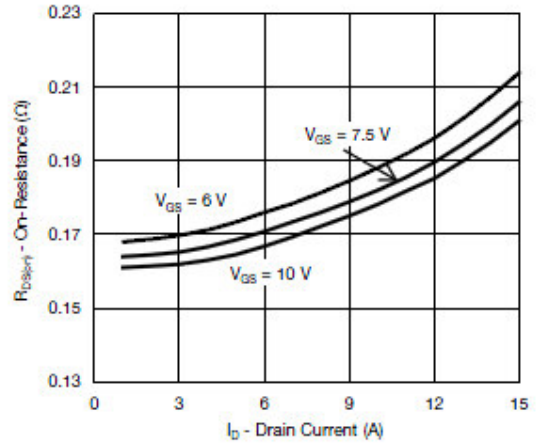
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> = -250uA	-100			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = -250uA	-1.0		-2.5	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -80V, V <sub>GS</sub> =0V			-1	
		V <sub>DS</sub> = -80V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			-30	uA
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ -10V, V <sub>GS</sub> = -10V	-8			A
Drain-Source On-Resistance	R <sub>Ds(on)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> =-3.8A		235	260	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> =-2.6A		255	290	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = -15V, I <sub>D</sub> = -3.2A		12		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -2A, V <sub>GS</sub> =0V		-0.8	-1.3	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-50V, V <sub>GS</sub> =-4.5V I <sub>D</sub> = -2.6A		12	20	nC
Gate-Source Charge	Q <sub>gs</sub>			3.0		
Gate-Drain Charge	Q <sub>gd</sub>			4.5		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-50V, V <sub>GS</sub> =0V f=1MHz		1100		pF
Output Capacitance	C <sub>oss</sub>			70		
Reverse Transfer Capacitance	C <sub>rss</sub>			45		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-50V, R <sub>L</sub> =17Ω I <sub>D</sub> ≡ -2.6A, V <sub>GEN</sub> =-10V R <sub>G</sub> =1Ω		8	15	ns
	t <sub>r</sub>			15	20	
Turn-Off Time	t <sub>d(off)</sub>			35	50	
	t <sub>f</sub>			10	25	



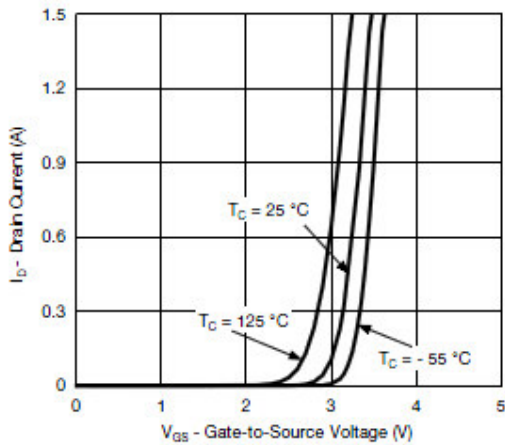
## Typical Characteristics



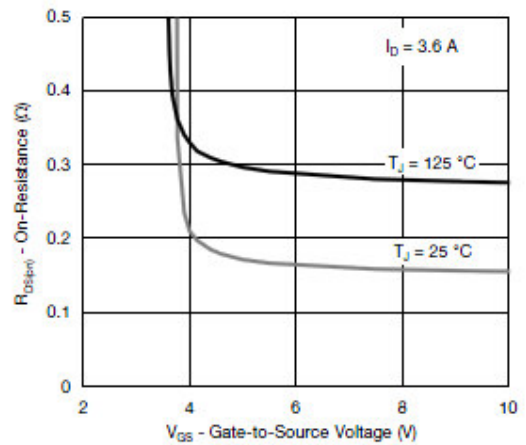
Output Characteristics



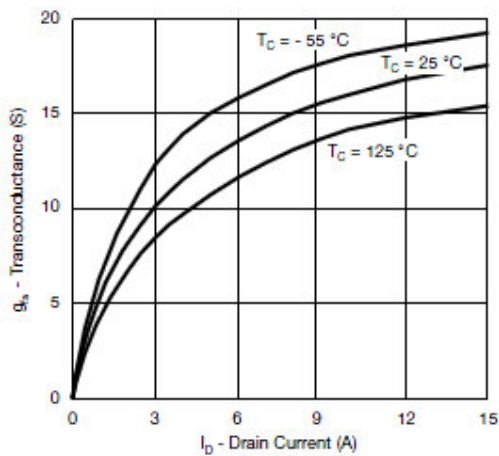
On-Resistance vs. Drain Current



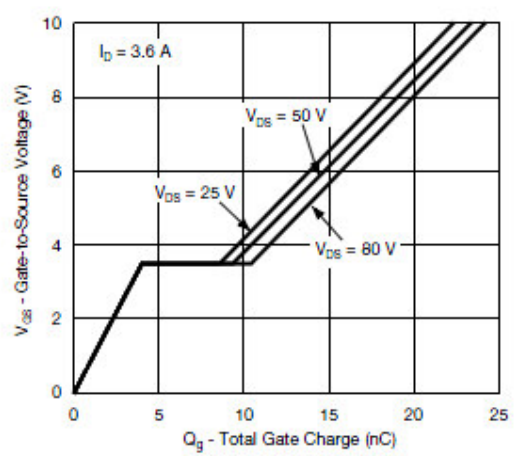
Transfer Characteristics



On-Resistance vs. Gate-to-Source Voltage



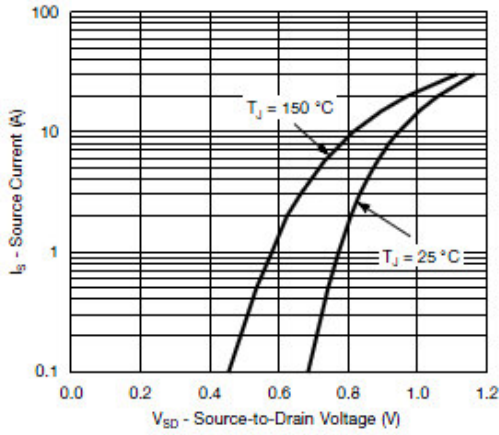
Transconductance



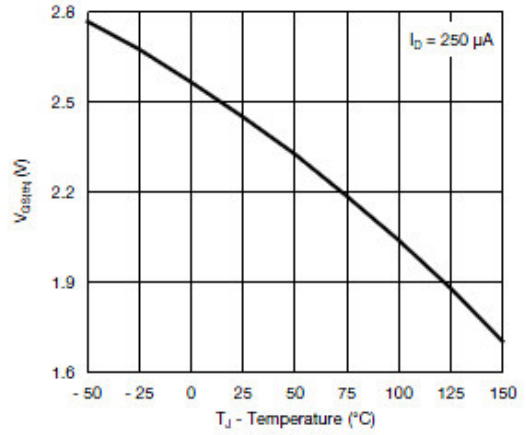
Gate Charge



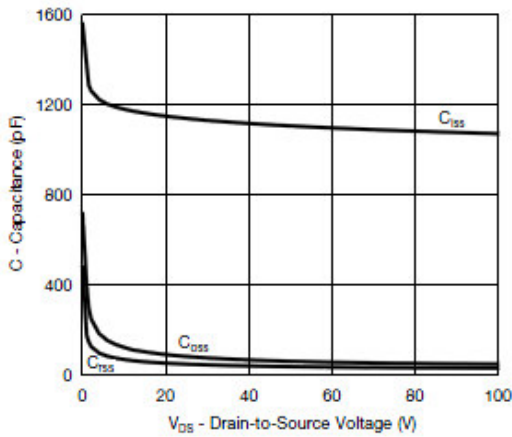
## Typical Characteristics



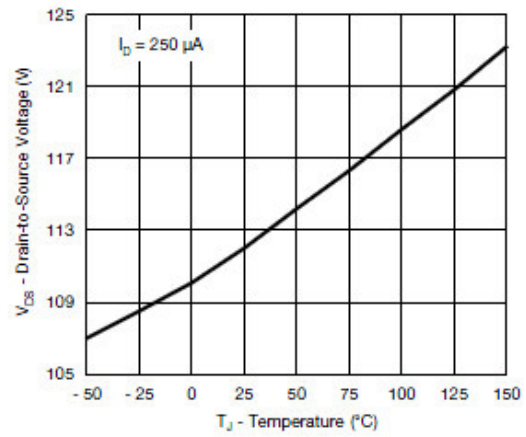
Source-Drain Diode Forward Voltage



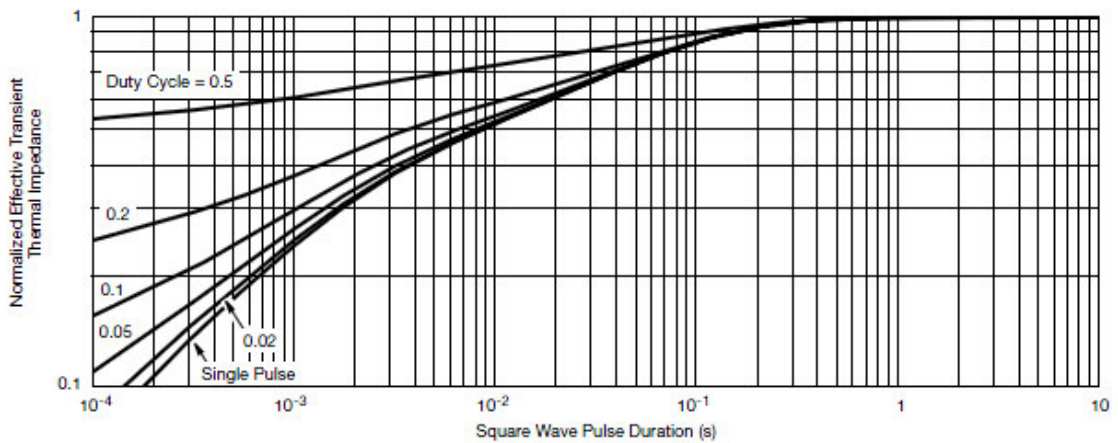
Threshold Voltage



Capacitance



Drain Source Breakdown vs. Junction Temperature

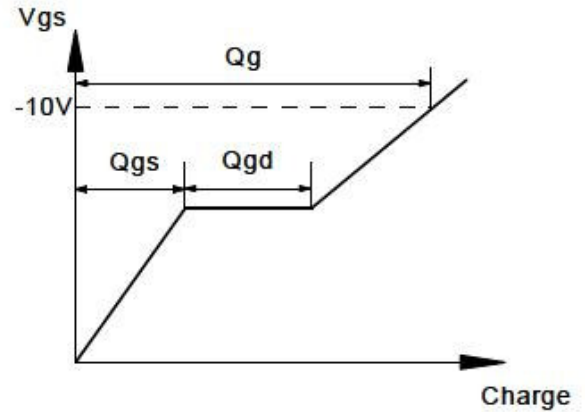
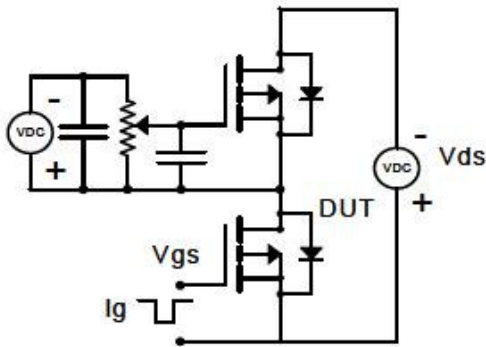


Normalized Thermal Transient Impedance, Junction-to-Case

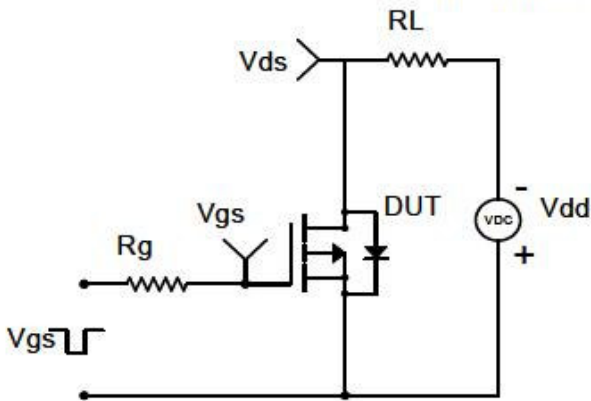


## Typical Characteristics

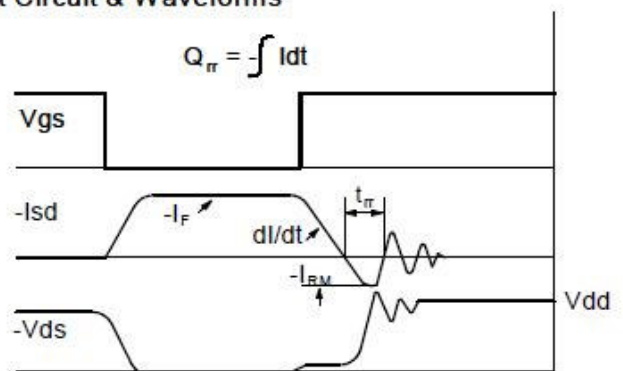
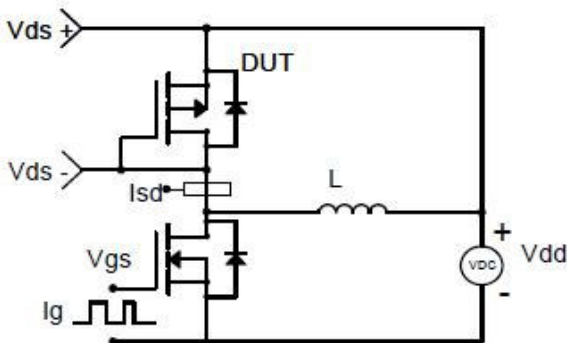
### Gate Charge Test Circuit & Waveform



### Resistive Switching Test Circuit & Waveforms

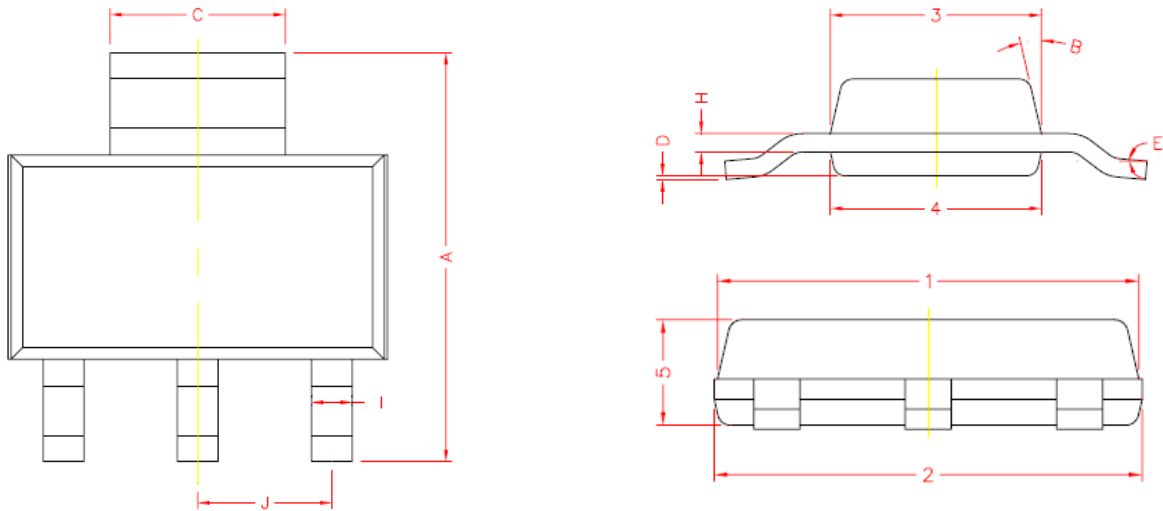


### Diode Recovery Test Circuit & Waveforms





**Package Information ( SOT-223 )**



REF.	DIMENSIONS	
	Millimeters	
	Min.	Max.
A	6.70	7.30
C	2.90	3.10
D	0.02	0.10
E	0*	10*
I	0.60	0.80
H	0.25	0.35
B	13° TYP.	
J	2.30 REF.	
1	6.30	6.70
2	6.30	6.70
3	3.30	3.70
4	3.30	3.70
5	1.40	1.80

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